



Rev.A No

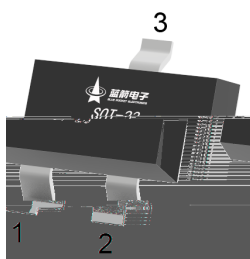
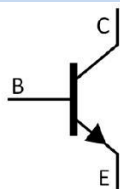
SOT-23

Silicon NPN transistor in a SOT-23 Plastic Package.

400V AEC-Q101

Moisture S Human Body Model; 4 kV, Machine Model; 400 V, Qualified to AEC-Q

I_c
Medium power Medium power currents up to 500 mA, Meet the stringent requirements of au



PIN 1 Base

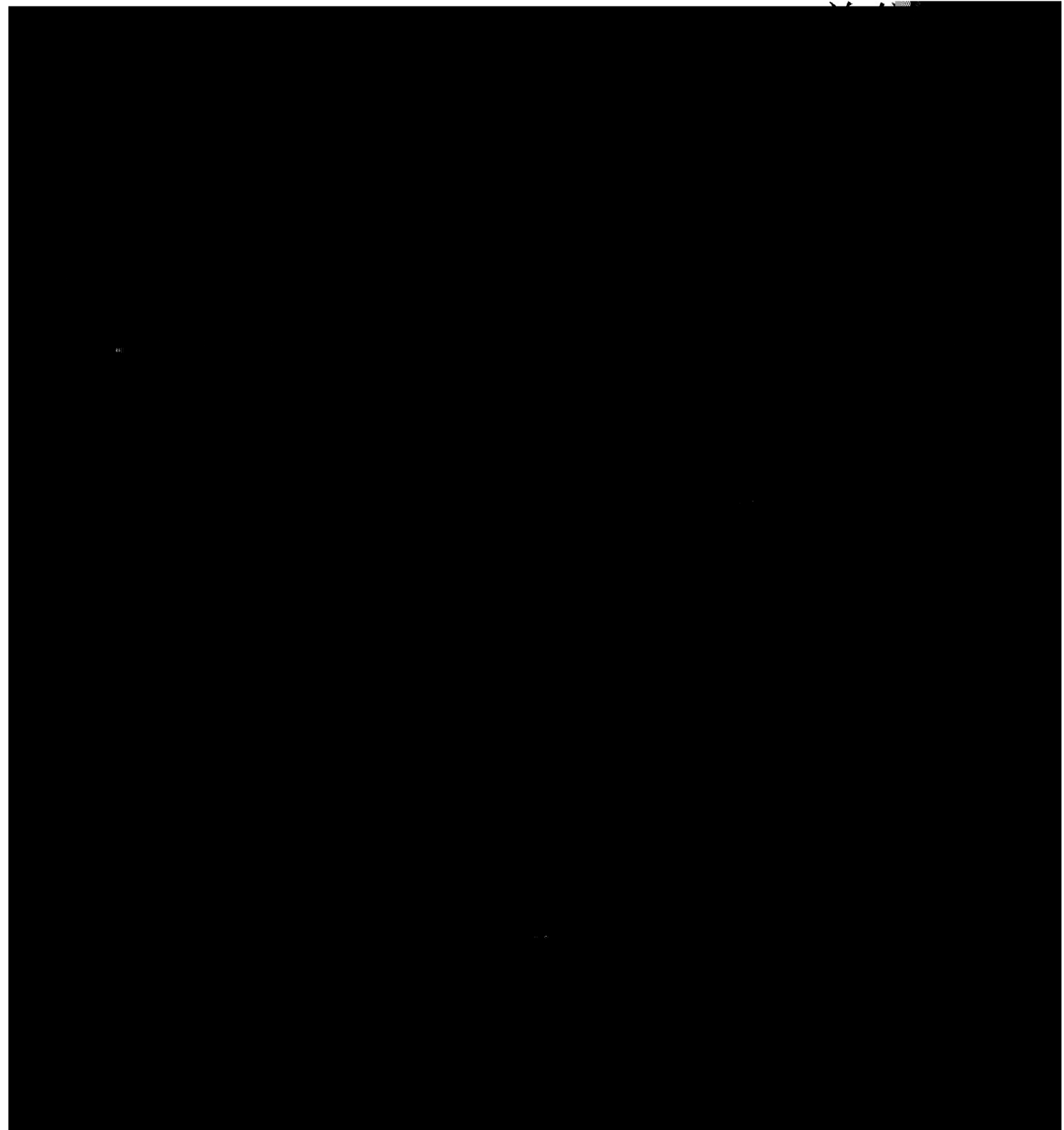
h_{FE} Range	100 300
Marking	Q2X

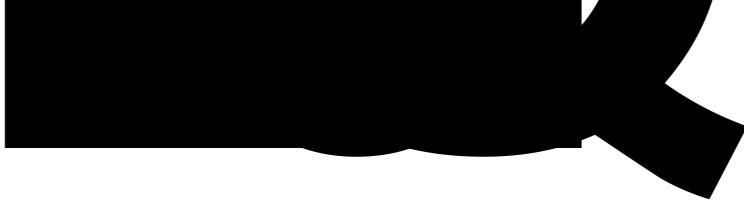


Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

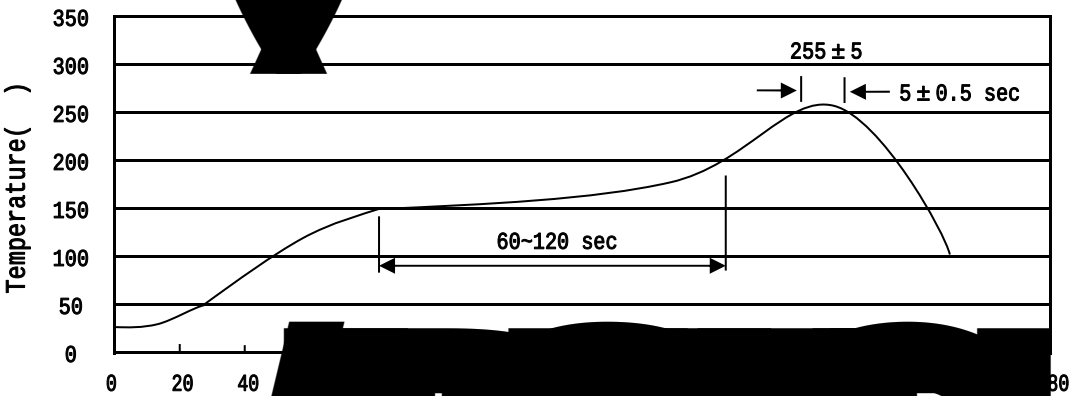
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	40			V
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ I_C				







Temperature Profile for IR Reflow Soldering(Pb-Free)



- 1 150
- 2 255
- 3

260± Time:10±1 sec

Package Type	Dimension (unit mm ³)	
	Inner Boxes/Outer Box	Units/Outer Box
SOT-23	6	180,000